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1K SPI Bus Serial EEPROM

Device Selection Table

Part Number	Vcc Range	Page Size	Temp. Ranges	Packages
25AA010A	1.8-5.5V	16 Bytes	I	P, MS, SN, ST, MN, MC, OT
25LC010A	2.5-5.5V	16 Bytes	I, E	P, MS, SN, ST, MN, MC, OT

Features:

- 10 MHz max. Clock Frequency
- Low-Power CMOS Technology:
 - Max. Write Current: 5 mA at 5.5V, 10 MHz
 - Read Current: 5 mA at 5.5V, 10 MHz
 - Standby Current: 5 μ A at 5.5V
- 128 x 8-bit Organization
- Write Page mode (up to 16 bytes)
- Sequential Read
- Self-Timed Erase and Write Cycles (5 ms max.)
- Block Write Protection:
 - Protect none, 1/4, 1/2 or all of array
- Built-In Write Protection:
 - Power-on/off data protection circuitry
 - Write enable latch
 - Write-protect pin
- High Reliability:
 - Endurance: 1,000,000 Erase/Write cycles
 - Data retention: > 200 years
 - ESD protection: > 4000V
- Temperature Ranges Supported:
 - Industrial (I): -40°C to +85°C
 - Automotive (E): -40°C to +125°C
- Pb-Free and RoHS Compliant

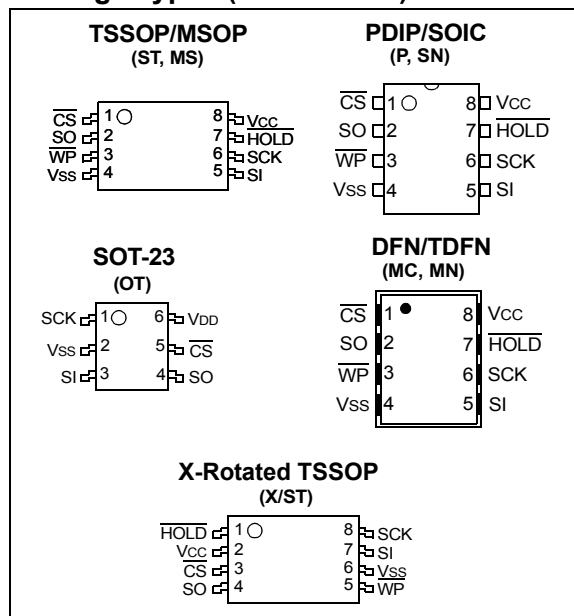
Description:

The Microchip Technology Inc. 25XX010A* is a 1 Kbit Serial Electrically Erasable Programmable Read-Only Memory (EEPROM). The memory is accessed via a simple Serial Peripheral Interface (SPI) compatible serial bus. The bus signals required are a clock input (SCK) plus separate data in (SI) and data out (SO) lines. Access to the device is controlled through a Chip Select (CS) input.

Communication to the device can be paused via the hold pin (HOLD). While the device is paused, transitions on its inputs will be ignored, with the exception of Chip Select, allowing the host to service higher priority interrupts.

The 25XX010A is available in standard packages including 8-lead PDIP and SOIC, and advanced packages including 8-lead MSOP, 8-lead TSSOP and rotated TSSOP, 8-lead 2x3 DFN and TDFN, and 6-lead SOT-23.

Package Types (not to scale)



*25XX010A is used in this document as a generic part number for the 25AA010A and the 25LC010A.

Pin Function Table

Name	Function
CS	Chip Select Input
SO	Serial Data Output
WP	Write-Protect
Vss	Ground
SI	Serial Data Input
SCK	Serial Clock Input
HOLD	Hold Input
Vcc	Supply Voltage

25AA010A/25LC010A

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings^(†)

V _{CC}	6.5V
All inputs and outputs w.r.t. V _{SS}	-0.6V to V _{CC} +1.0V
Storage temperature	-65°C to 150°C
Ambient temperature under bias	-40°C to 125°C
ESD protection on all pins	4 kV

† NOTICE: Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for an extended period of time may affect device reliability.

TABLE 1-1: DC CHARACTERISTICS

DC CHARACTERISTICS			Industrial (I): TA = -40°C to +85°C		V _{CC} = 1.8V to 5.5V	
			Automotive (E): TA = -40°C to +125°C		V _{CC} = 2.5V to 5.5V	
Param. No.	Sym.	Characteristic	Min.	Max.	Units	Test Conditions
D001	V _{IH1}	High-level input voltage	0.7 V _{CC}	V _{CC} +1	V	
D002	V _{IL1}	Low-level input voltage	-0.3	0.3 V _{CC}	V	V _{CC} ≥ 2.7V (Note)
D003	V _{IL2}		-0.3	0.2 V _{CC}	V	V _{CC} < 2.7V (Note)
D004	V _{OL}	Low-level output voltage	—	0.4	V	I _{OL} = 2.1 mA
D005	V _{OL}		—	0.2	V	I _{OL} = 1.0 mA, V _{CC} < 2.5V
D006	V _{OH}	High-level output voltage	V _{CC} -0.5	—	V	I _{OH} = -400 μA
D007	I _{LI}	Input leakage current	—	±1	μA	\overline{CS} = V _{CC} , V _{IN} = V _{SS} or V _{CC}
D008	I _{LO}	Output leakage current	—	±1	μA	\overline{CS} = V _{CC} , V _{OUT} = V _{SS} or V _{CC}
D009	C _{INT}	Internal capacitance (all inputs and outputs)	—	7	pF	TA = 25°C, CLK = 1.0 MHz, V _{CC} = 5.0V (Note)
D010	I _{CC Read}	Operating current	—	5	mA	V _{CC} = 5.5V; F _{CLK} = 10.0 MHz; SO = Open
			—	2.5	mA	V _{CC} = 2.5V; F _{CLK} = 5.0 MHz; SO = Open
D011	I _{CC Write}		—	5	mA	V _{CC} = 5.5V
			—	3	mA	V _{CC} = 2.5V
D012	I _{CCS}	Standby current	—	5	μA	\overline{CS} = V _{CC} = 5.5V, Inputs tied to V _{CC} or V _{SS} , TA = +125°C
			—	1	μA	\overline{CS} = V _{CC} = 2.5V, Inputs tied to V _{CC} or V _{SS} , TA = +85°C

Note: This parameter is periodically sampled and not 100% tested.

TABLE 1-2: AC CHARACTERISTICS

AC CHARACTERISTICS			Industrial (I): TA = -40°C to +85°C VCC = 1.8V to 5.5V Automotive (E): TA = -40°C to +125°C VCC = 2.5V to 5.5V			
Param. No.	Sym.	Characteristic	Min.	Max.	Units	Test Conditions
1	FCLK	Clock frequency	—	10	MHz	4.5V ≤ VCC < 5.5V
			—	5	MHz	2.5V ≤ VCC < 4.5V
			—	3	MHz	1.8V ≤ VCC < 2.5V
2	TCSS	$\overline{\text{CS}}$ setup time	50	—	ns	4.5V ≤ VCC < 5.5V
			100	—	ns	2.5V ≤ VCC < 4.5V
			150	—	ns	1.8V ≤ VCC < 2.5V
3	TCSH	$\overline{\text{CS}}$ hold time	100	—	ns	4.5V ≤ VCC < 5.5V
			200	—	ns	2.5V ≤ VCC < 4.5V
			250	—	ns	1.8V ≤ VCC < 2.5V
4	TCSD	$\overline{\text{CS}}$ disable time	50	—	ns	—
5	Tsu	Data setup time	10	—	ns	4.5V ≤ VCC < 5.5V
			20	—	ns	2.5V ≤ VCC < 4.5V
			30	—	ns	1.8V ≤ VCC < 2.5V
6	THD	Data hold time	20	—	ns	4.5V ≤ VCC < 5.5V
			40	—	ns	2.5V ≤ VCC < 4.5V
			50	—	ns	1.8V ≤ VCC < 2.5V
7	TR	CLK rise time	—	100	ns	(Note 1)
8	TF	CLK fall time	—	100	ns	(Note 1)
9	THI	Clock high time	50	—	ns	4.5V ≤ VCC < 5.5V
			100	—	ns	2.5V ≤ VCC < 4.5V
			150	—	ns	1.8V ≤ VCC < 2.5V
10	TLO	Clock low time	50	—	ns	4.5V ≤ VCC < 5.5V
			100	—	ns	2.5V ≤ VCC < 4.5V
			150	—	ns	1.8V ≤ VCC < 2.5V
11	TCLD	Clock delay time	50	—	ns	—
12	TCLE	Clock enable time	50	—	ns	—
13	TV	Output valid from clock low	—	50	ns	4.5V ≤ VCC < 5.5V
			—	100	ns	2.5V ≤ VCC < 4.5V
			—	160	ns	1.8V ≤ VCC < 2.5V
14	THO	Output hold time	0	—	ns	(Note 1)
15	TDis	Output disable time	—	40	ns	4.5V ≤ VCC < 5.5V (Note 1)
			—	80	ns	2.5V ≤ VCC < 4.5V (Note 1)
			—	160	ns	1.8V ≤ VCC < 2.5V (Note 1)
16	THS	$\overline{\text{HOLD}}$ setup time	20	—	ns	4.5V ≤ VCC < 5.5V
			40	—	ns	2.5V ≤ VCC < 4.5V
			80	—	ns	1.8V ≤ VCC < 2.5V

Note 1: This parameter is periodically sampled and not 100% tested.

2: This parameter is not tested but ensured by characterization. For endurance estimates in a specific application, please consult the Total Endurance™ Model which can be obtained from Microchip's web site: www.microchip.com.

3: Twc begins on the rising edge of $\overline{\text{CS}}$ after a valid write sequence and ends when the internal write cycle is complete.

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TABLE 1-2: AC CHARACTERISTICS (CONTINUED)

AC CHARACTERISTICS			Industrial (I): TA = -40°C to +85°C VCC = 1.8V to 5.5V Automotive (E): TA = -40°C to +125°C VCC = 2.5V to 5.5V			
Param. No.	Sym.	Characteristic	Min.	Max.	Units	Test Conditions
17	THH	$\overline{\text{HOLD}}$ hold time	20	—	ns	$4.5V \leq V_{CC} < 5.5V$
			40	—	ns	$2.5V \leq V_{CC} < 4.5V$
			80	—	ns	$1.8V \leq V_{CC} < 2.5V$
18	THZ	$\overline{\text{HOLD}}$ low to output high-Z	30	—	ns	$4.5V \leq V_{CC} < 5.5V$ (Note 1)
			60	—	ns	$2.5V \leq V_{CC} < 4.5V$ (Note 1)
			160	—	ns	$1.8V \leq V_{CC} < 2.5V$ (Note 1)
19	THV	$\overline{\text{HOLD}}$ high to output valid	30	—	ns	$4.5V \leq V_{CC} < 5.5V$
			60	—	ns	$2.5V \leq V_{CC} < 4.5V$
			160	—	ns	$1.8V \leq V_{CC} < 2.5V$
20	Twc	Internal write cycle time (byte or page)	—	5	ms	(Note 3)
21	—	Endurance	1M	—	E/W Cycles	25°C, VCC = 5.5V (Note 2)

Note 1: This parameter is periodically sampled and not 100% tested.

2: This parameter is not tested but ensured by characterization. For endurance estimates in a specific application, please consult the Total Endurance™ Model which can be obtained from Microchip's web site: www.microchip.com.

3: Twc begins on the rising edge of $\overline{\text{CS}}$ after a valid write sequence and ends when the internal write cycle is complete.

TABLE 1-3: AC TEST CONDITIONS

AC Waveform:	
VLO = 0.2V	—
VHI = VCC - 0.2V	(Note 1)
VHI = 4.0V	(Note 2)
CL = 100 pF	—
Timing Measurement Reference Level	
Input	0.5 VCC
Output	0.5 VCC

Note 1: For VCC ≤ 4.0V

2: For VCC > 4.0V

FIGURE 1-1: HOLD TIMING

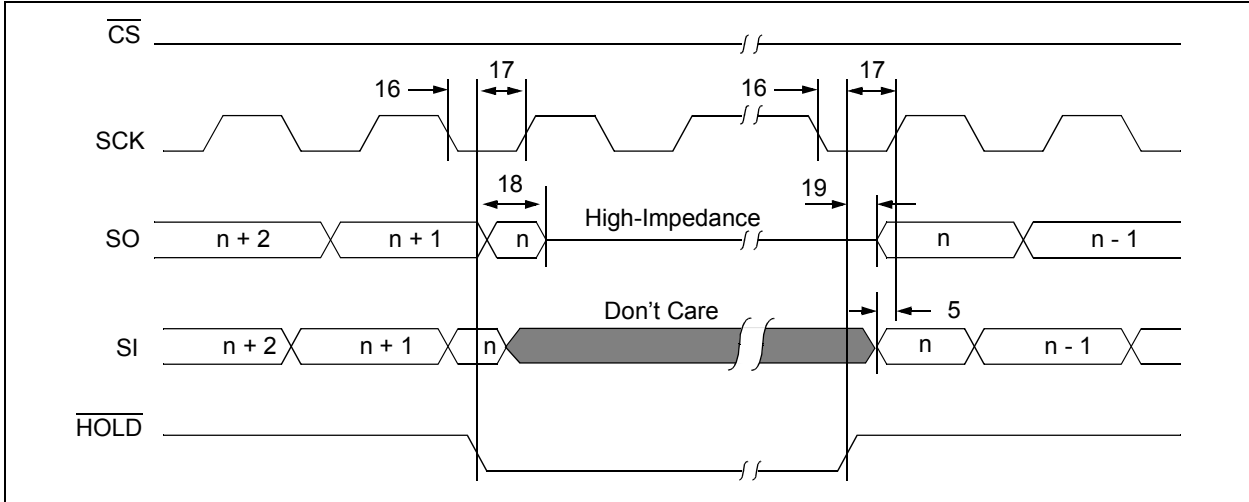


FIGURE 1-2: SERIAL INPUT TIMING

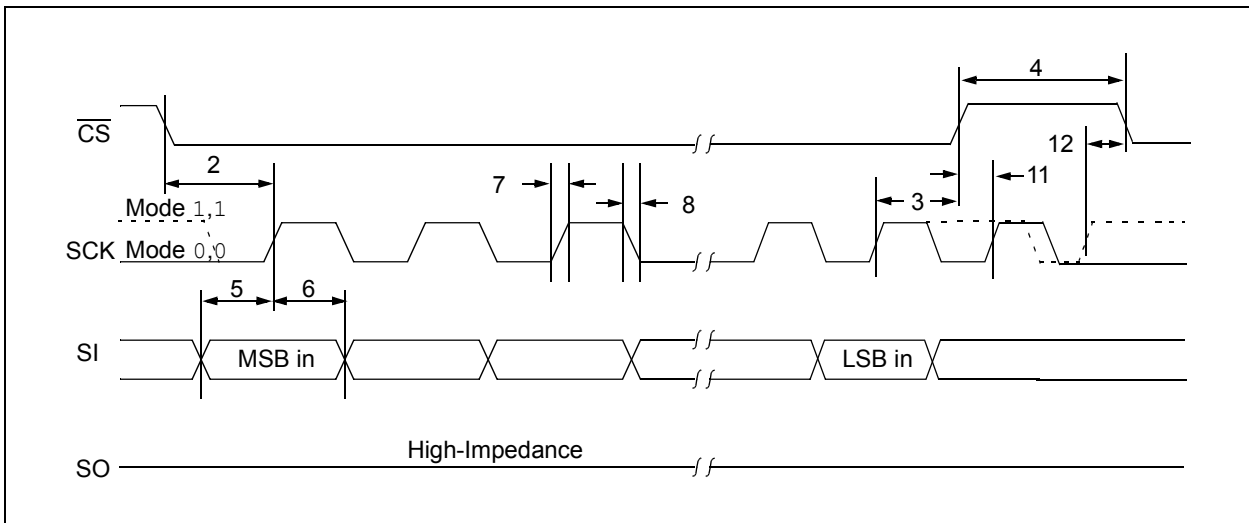
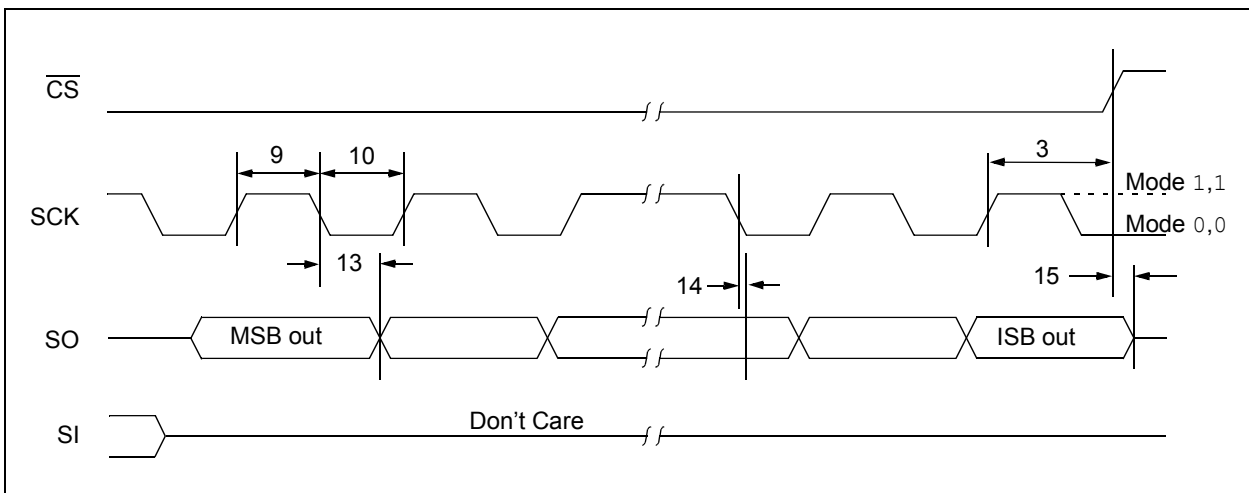


FIGURE 1-3: SERIAL OUTPUT TIMING



25AA010A/25LC010A

2.0 FUNCTIONAL DESCRIPTION

2.1 Principles of Operation

The 25XX010A is a 128 byte Serial EEPROM designed to interface directly with the Serial Peripheral Interface (SPI) port of many of today's popular microcontroller families, including Microchip's PIC[®] microcontrollers. It may also interface with microcontrollers that do not have a built-in SPI port by using discrete I/O lines programmed properly in firmware to match the SPI protocol.

The 25XX010A contains an 8-bit instruction register. The device is accessed via the SI pin, with data being clocked in on the rising edge of SCK. The $\overline{\text{CS}}$ pin must be low and the HOLD pin must be high for the entire operation.

Table 2-1 contains a list of the possible instruction bytes and format for device operation. All instructions, addresses, and data are transferred MSb first, LSb last.

Data (SI) is sampled on the first rising edge of SCK after $\overline{\text{CS}}$ goes low. If the clock line is shared with other peripheral devices on the SPI bus, the user can assert the HOLD input and place the 25XX010A in 'HOLD' mode. After releasing the HOLD pin, operation will resume from the point when the HOLD was asserted.

2.2 Read Sequence

The device is selected by pulling $\overline{\text{CS}}$ low. The 8-bit READ instruction is transmitted to the 25XX010A followed by an 8-bit address. See Figure 2-1 for more details.

After the correct READ instruction and address are sent, the data stored in the memory at the selected address is shifted out on the SO pin. Data stored in the memory at the next address can be read sequentially by continuing to provide clock pulses to the slave. The internal Address Pointer automatically increments to the next higher address after each byte of data is shifted out. When the highest address is reached (7Fh), the address counter rolls over to address 00h allowing the read cycle to be continued indefinitely. The read operation is terminated by raising the $\overline{\text{CS}}$ pin (Figure 2-1).

2.3 Write Sequence

Prior to any attempt to write data to the 25XX010A, the write enable latch must be set by issuing the WREN instruction (Figure 2-4). This is done by setting $\overline{\text{CS}}$ low and then clocking out the proper instruction into the 25XX010A. After all eight bits of the instruction are transmitted, $\overline{\text{CS}}$ must be driven high to set the write enable latch. If the write operation is initiated immediately after the WREN instruction without $\overline{\text{CS}}$ driven high, data will not be written to the array since the write enable latch was not properly set.

After setting the write enable latch, the user may proceed by driving $\overline{\text{CS}}$ low, issuing a WRITE instruction, followed by the remainder of the address, and then the data to be written. Up to 16 bytes of data can be sent to the device before a write cycle is necessary. The only restriction is that all of the bytes must reside in the same page. Additionally, a page address begins with XXXX 0000 and ends with XXXX 1111. If the internal address counter reaches XXXX 1111 and clock signals continue to be applied to the chip, the address counter will roll back to the first address of the page and overwrite any data that previously existed in those locations.

Note: Page write operations are limited to writing bytes within a single physical page, **regardless** of the number of bytes actually being written. Physical page boundaries start at addresses that are integer multiples of the page buffer size (or 'page size') and, end at addresses that are integer multiples of page size - 1. If a Page Write command attempts to write across a physical page boundary, the result is that the data wraps around to the beginning of the current page (overwriting data previously stored there), instead of being written to the next page as might be expected. It is therefore necessary for the application software to prevent page write operations that would attempt to cross a page boundary.

For the data to be actually written to the array, the $\overline{\text{CS}}$ must be brought high after the Least Significant bit (D0) of the n^{th} data byte has been clocked in. If $\overline{\text{CS}}$ is driven high at any other time, the write operation will not be completed. Refer to Figure 2-2 and Figure 2-3 for more detailed illustrations on the byte write sequence and the page write sequence, respectively. While the write is in progress, the STATUS register may be read to check the status of the WIP, WEL, BP1 and BP0 bits (Figure 2-6). Attempting to read a memory array location will not be possible during a write cycle. Polling the WIP bit in the STATUS register is recommended in order to determine if a write cycle is in progress. When the write cycle is completed, the write enable latch is reset.

BLOCK DIAGRAM

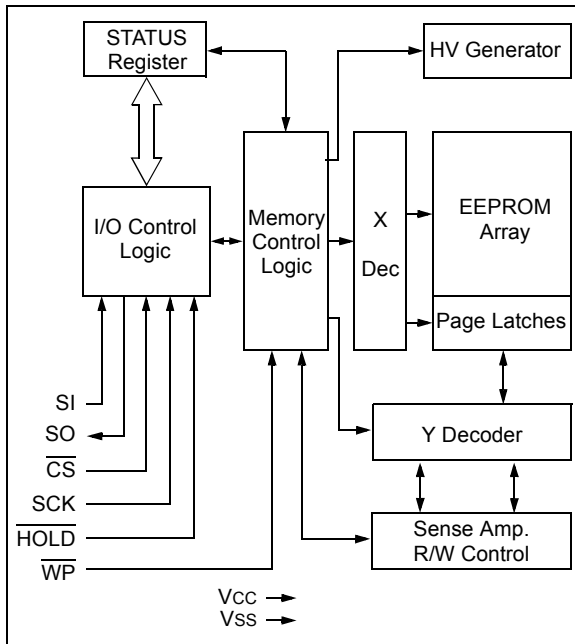
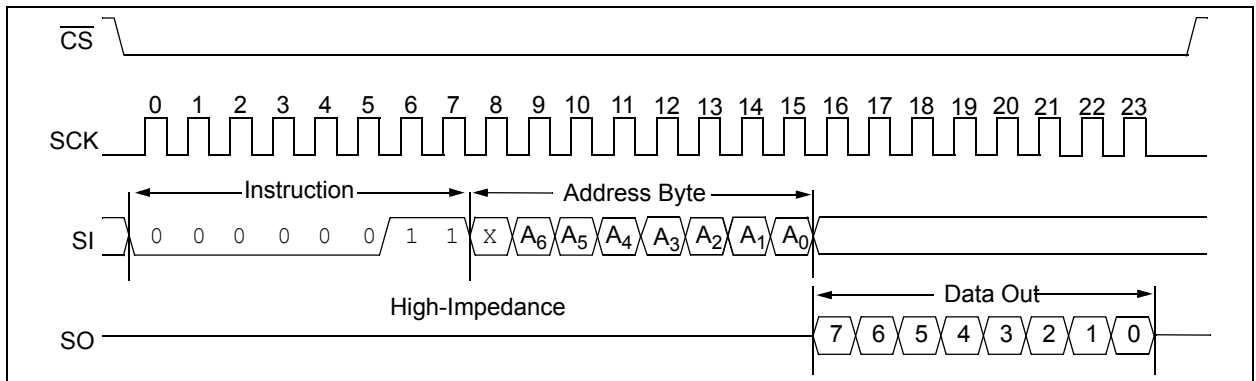


TABLE 2-1: INSTRUCTION SET

Instruction Name	Instruction Format	Description
READ	0000 x011	Read data from memory array beginning at selected address
WRITE	0000 x010	Write data to memory array beginning at selected address
WRDI	0000 x100	Reset the write enable latch (disable write operations)
WREN	0000 x110	Set the write enable latch (enable write operations)
RDSR	0000 x101	Read STATUS register
WRSR	0000 x001	Write STATUS register

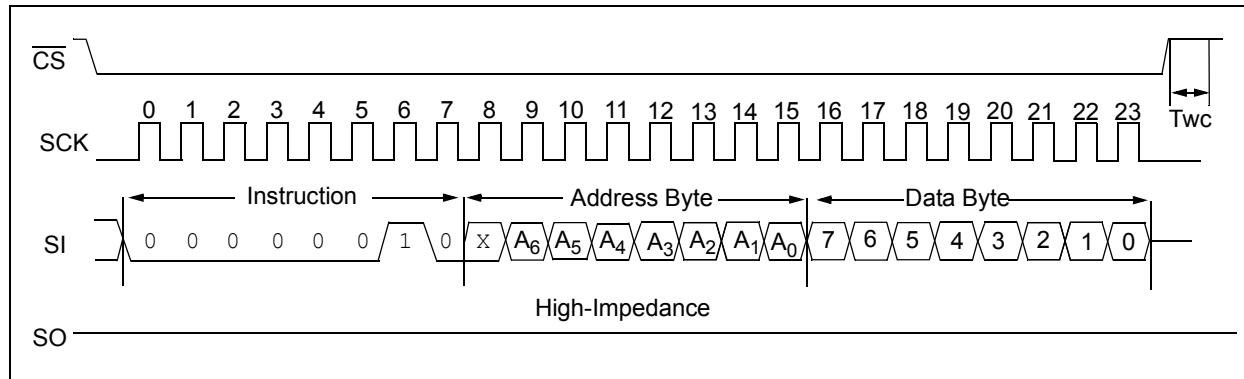
x = don't care

FIGURE 2-1: READ SEQUENCE



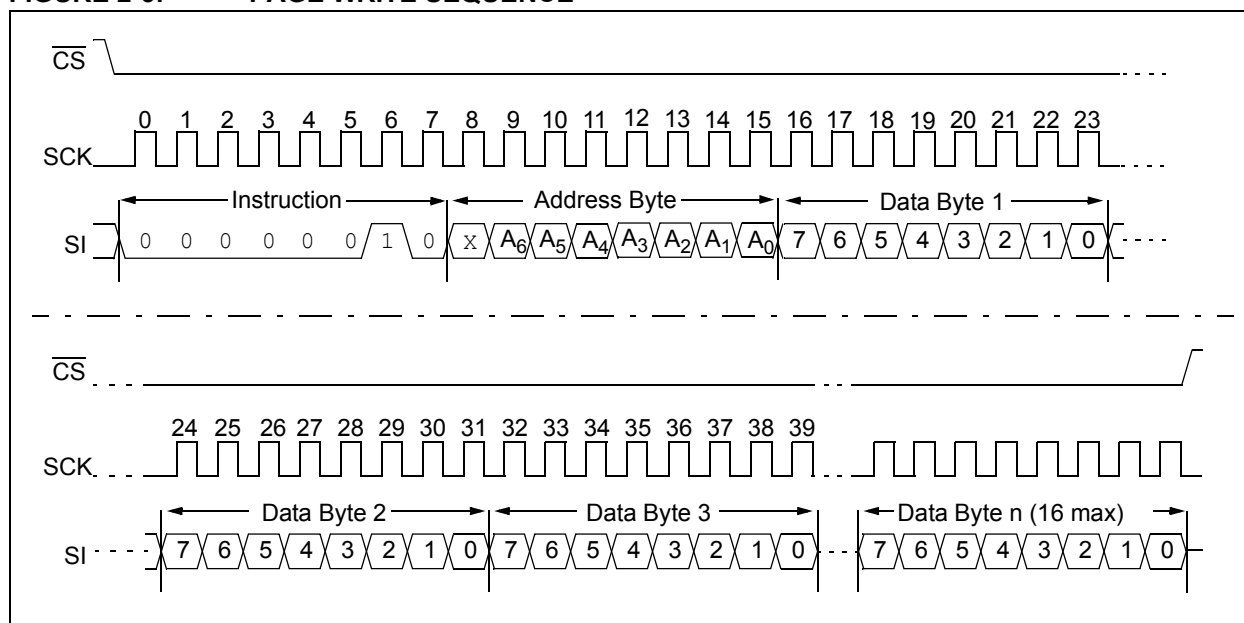
25AA010A/25LC010A

FIGURE 2-2: BYTE WRITE SEQUENCE



x = don't care

FIGURE 2-3: PAGE WRITE SEQUENCE



x = don't care

2.4 Write Enable (WREN) and Write Disable (WRDI)

The 25XX010A contains a write enable latch. See [Table 2-4](#) for the Write-Protect Functionality Matrix. This latch must be set before any write operation will be completed internally. The WREN instruction will set the latch, and the WRDI will reset the latch.

The following is a list of conditions under which the write enable latch will be reset:

- Power-up
- WRDI instruction successfully executed
- WRSR instruction successfully executed
- WRITE instruction successfully executed
- \overline{WP} pin is brought low

FIGURE 2-4: WRITE ENABLE SEQUENCE (WREN)

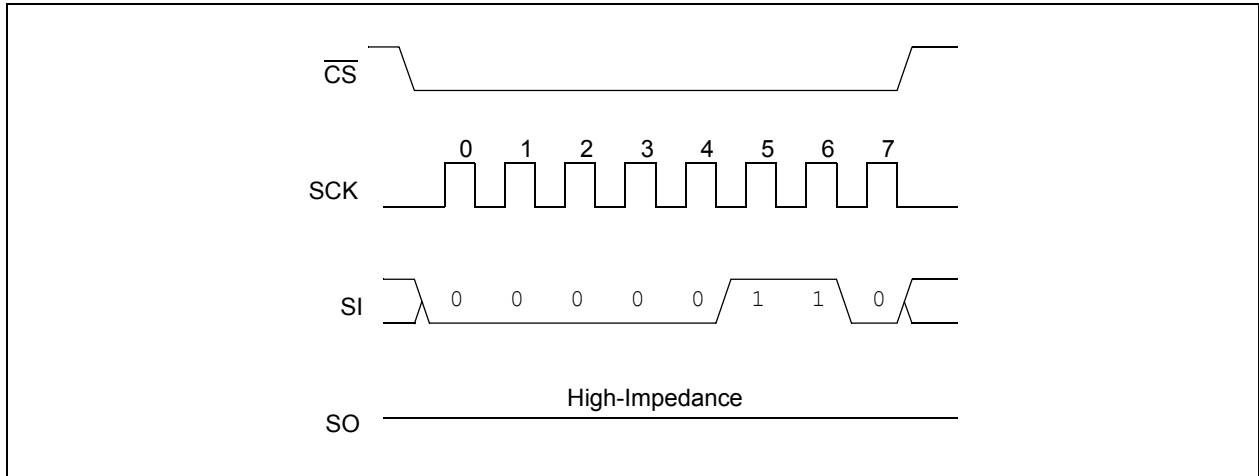
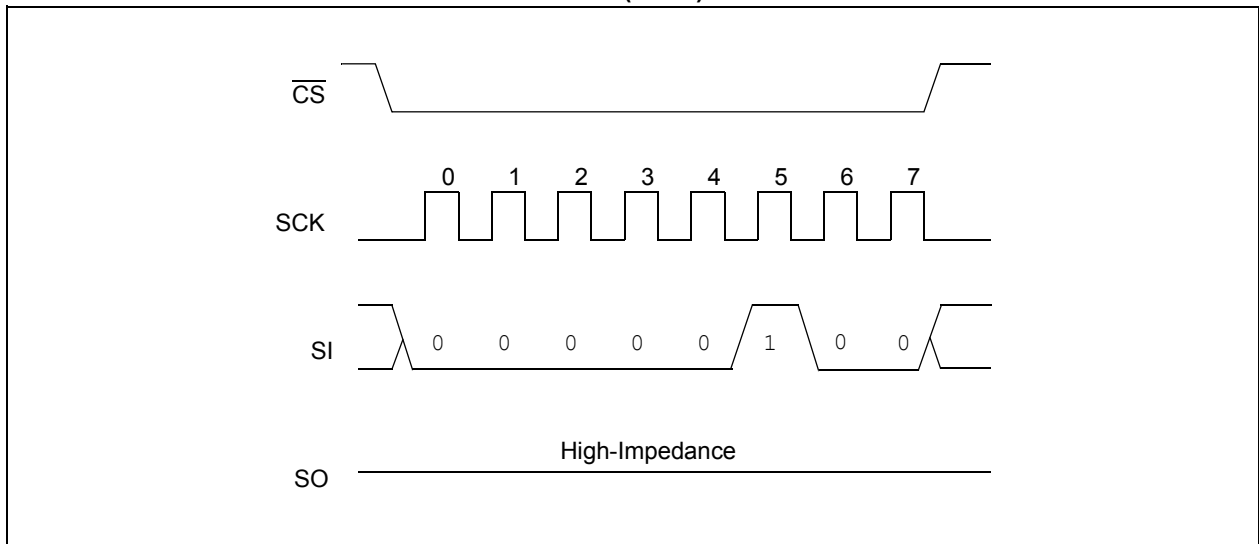


FIGURE 2-5: WRITE DISABLE SEQUENCE (WRDI)



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2.5 Read Status Register Instruction (RDSR)

The Read Status Register instruction (RDSR) provides access to the STATUS register. See [Figure 2-6](#) for the RDSR timing sequence. The STATUS register may be read at any time, even during a write cycle. The STATUS register is formatted as follows:

TABLE 2-2: STATUS REGISTER

7	6	5	4	3	2	1	0
–	–	–	–	W/R	W/R	R	R
X	X	X	X	BP1	BP0	WEL	WIP

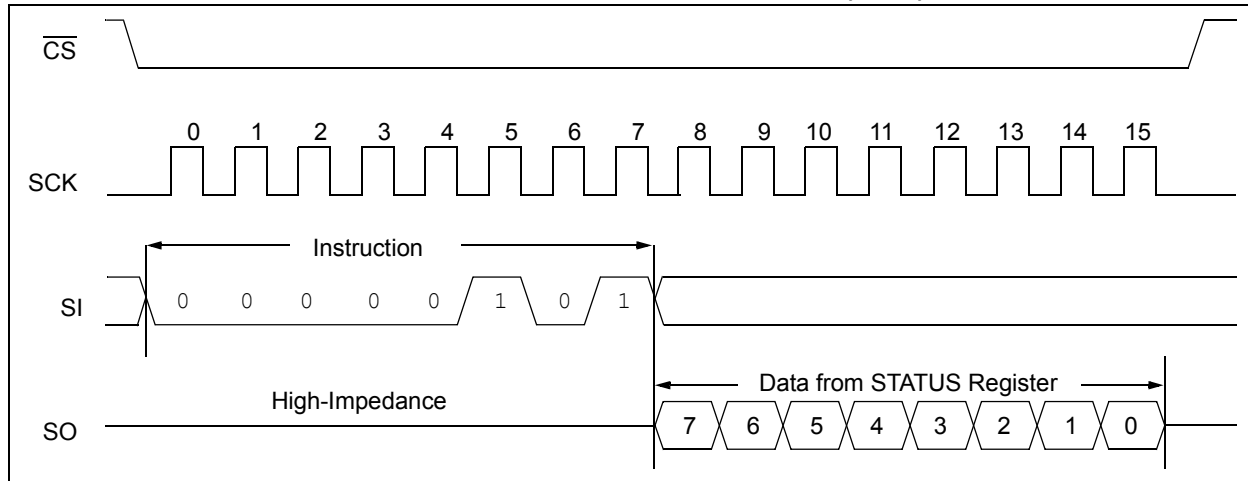
W/R = writable/readable. R = read-only.

The **Write-In-Process (WIP)** bit indicates whether the 25XX010A is busy with a write operation. When set to a '1', a write is in progress, when set to a '0', no write is in progress. This bit is read-only.

The **Write Enable Latch (WEL)** bit indicates the status of the write enable latch and is read-only. When set to a '1', the latch allows writes to the array, when set to a '0', the latch prohibits writes to the array. The state of this bit can always be updated via the WREN or WRDI commands regardless of the state of write protection on the STATUS register. These commands are shown in [Figure 2-4](#) and [Figure 2-5](#).

The **Block Protection (BP0 and BP1)** bits indicate which blocks are currently write-protected. These bits are set by the user issuing the WRSR instruction, which is shown in [Figure 2-7](#). These bits are nonvolatile and are described in more detail in [Table 2-3](#).

FIGURE 2-6: READ STATUS REGISTER TIMING SEQUENCE (RDSR)



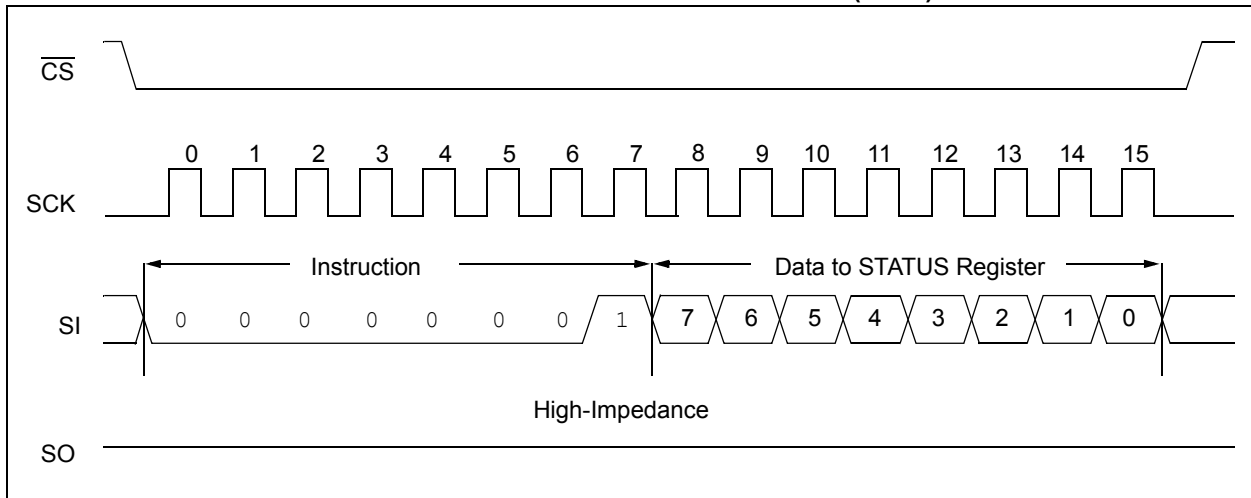
2.6 Write Status Register Instruction (WRSR)

The Write Status Register instruction (WRSR) allows the user to write to the nonvolatile bits in the STATUS register as shown in Table 2-2. See Figure 2-7 for the WRSR timing sequence. Four levels of protection for the array are selectable by writing to the appropriate bits in the STATUS register. The user has the ability to write-protect none, one, two or all four of the segments of the array as shown in Table 2-3.

TABLE 2-3: ARRAY PROTECTION

BP1	BP0	Array Addresses Write-Protected
0	0	none
0	1	upper 1/4 (60h-7Fh)
1	0	upper 1/2 (40h-7Fh)
1	1	all (00h-7Fh)

FIGURE 2-7: WRITE STATUS REGISTER TIMING SEQUENCE (WRSR)



Note: An internal write cycle (T_{wc}) is initiated on the rising edge of \overline{CS} after a valid write STATUS register sequence.

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2.7 Data Protection

The following protection has been implemented to prevent inadvertent writes to the array:

- The write enable latch is reset on power-up
- A write enable instruction must be issued to set the write enable latch
- After a byte write, page write or STATUS register write, the write enable latch is reset
- \overline{CS} must be set high after the proper number of clock cycles to start an internal write cycle
- Access to the array during an internal write cycle is ignored and programming is continued

2.8 Power-On State

The 25XX010A powers on in the following state:

- The device is in low-power Standby mode ($\overline{CS} = 1$)
- The write enable latch is reset
- SO is in high-impedance state
- A high-to-low-level transition on \overline{CS} is required to enter active state

TABLE 2-4: WRITE-PROTECT FUNCTIONALITY MATRIX

\overline{WP} (pin 3)	WEL (SR bit 1)	Protected Blocks	Unprotected Blocks	Status Register
0 (low)	x	Protected	Protected	Protected
1 (high)	0	Protected	Protected	Protected
1 (high)	1	Protected	Writable	Writable

x = don't care

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in [Table 3-1](#).

TABLE 3-1: PIN FUNCTION TABLE

Name	PDIP	SOIC	MSOP	TSSOP	DFN ⁽¹⁾	TDFN ⁽¹⁾	Rotated TSSOP	SOT-23	Function
$\overline{\text{CS}}$	1	1	1	1	1	1	3	5	Chip Select Input
SO	2	2	2	2	2	2	4	4	Serial Data Output
$\overline{\text{WP}}$	3	3	3	3	3	3	5	—	Write-Protect Pin
Vss	4	4	4	4	4	4	6	2	Ground
SI	5	5	5	5	5	5	7	3	Serial Data Input
SCK	6	6	6	6	6	6	8	1	Serial Clock Input
$\overline{\text{HOLD}}$	7	7	7	7	7	7	1	—	Hold Input
Vcc	8	8	8	8	8	8	2	6	Supply Voltage

Note 1: The exposed pad on the DFN/TDFN packages can be connected to Vss or left floating.

3.1 Chip Select ($\overline{\text{CS}}$)

A low level on this pin selects the device. A high level deselects the device and forces it into Standby mode. However, a programming cycle which is already initiated or in progress will be completed, regardless of the $\overline{\text{CS}}$ input signal. If $\overline{\text{CS}}$ is brought high during a program cycle, the device will go into Standby mode as soon as the programming cycle is complete. When the device is deselected, SO goes to the high-impedance state, allowing multiple parts to share the same SPI bus. A low-to-high transition on $\overline{\text{CS}}$ after a valid write sequence initiates an internal write cycle. After power-up, a low level on $\overline{\text{CS}}$ is required prior to any sequence being initiated.

3.2 Serial Output (SO)

The SO pin is used to transfer data out of the 25XX010A. During a read cycle, data is shifted out on this pin after the falling edge of the serial clock.

3.3 Write-Protect ($\overline{\text{WP}}$)

The $\overline{\text{WP}}$ pin is a hardware write-protect input pin. When it is low, all writes to the array or STATUS register are disabled, but any other operations function normally. When $\overline{\text{WP}}$ is high, all functions, including nonvolatile writes operate normally. At any time, when $\overline{\text{WP}}$ is low, the write enable Reset latch will be reset and programming will be inhibited. However, if a write cycle is already in progress, $\overline{\text{WP}}$ going low will not change or disable the write cycle. See Table 2-4 for the Write-Protect Functionality Matrix.

3.4 Serial Input (SI)

The SI pin is used to transfer data into the device. It receives instructions, addresses and data. Data is latched on the rising edge of the serial clock.

3.5 Serial Clock (SCK)

The SCK is used to synchronize the communication between a master and the 25XX010A. Instructions, addresses or data present on the SI pin are latched on the rising edge of the clock input, while data on the SO pin is updated after the falling edge of the clock input.

3.6 Hold ($\overline{\text{HOLD}}$)

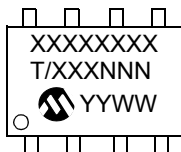
The $\overline{\text{HOLD}}$ pin is used to suspend transmission to the 25XX010A while in the middle of a serial sequence without having to retransmit the entire sequence again. It must be held high any time this function is not being used. Once the device is selected and a serial sequence is underway, the $\overline{\text{HOLD}}$ pin may be pulled low to pause further serial communication without resetting the serial sequence. The $\overline{\text{HOLD}}$ pin must be brought low while SCK is low, otherwise the $\overline{\text{HOLD}}$ function will not be invoked until the next SCK high-to-low transition. The 25XX010A must remain selected during this sequence. The SI, SCK and SO pins are in a high-impedance state during the time the device is paused and transitions on these pins will be ignored. To resume serial communication, $\overline{\text{HOLD}}$ must be brought high while the SCK pin is low, otherwise serial communication will not resume. Lowering the $\overline{\text{HOLD}}$ line at any time will tri-state the SO line.

25AA010A/25LC010A

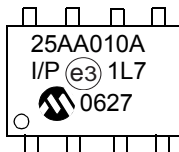
4.0 PACKAGING INFORMATION

4.1 Package Marking Information

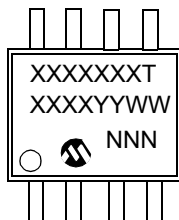
8-Lead PDIP



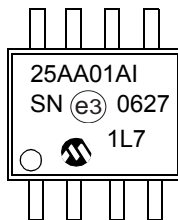
Example:



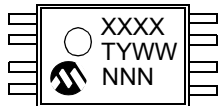
8-Lead SOIC



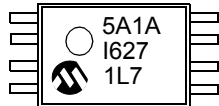
Example:



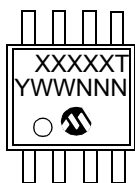
8-Lead TSSOP



Example:



8-Lead MSOP (150 mil)



Example:



Part Number	1st Line Marking Codes								
	TSSOP		MSOP	SOT-23		DFN		TDFN	
	Standard	Rotated		I Temp.	E Temp.	I Temp.	E. Temp.	I Temp.	E. Temp.
25AA010A	5A1A	A1AX	5A1AT	12NN	—	401	—	C01	—
25LC010A	5L1A	L1AX	5L1AT	15NN	16NN	404	405	C04	C05

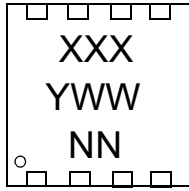
Note: T = Temperature grade (I, E) NN = Alphanumeric traceability code

Legend:	XX...X	Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

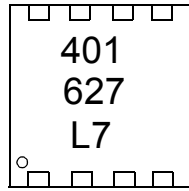
Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

Package Marking Information (continued)

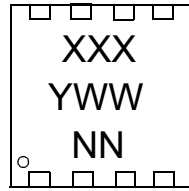
8-Lead 2X3 DFN



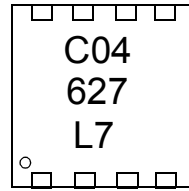
Example:



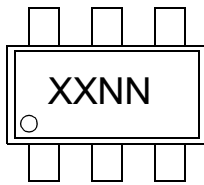
8-Lead 2X3 TDFN



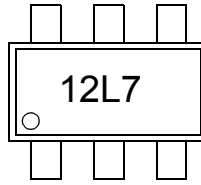
Example:



6-Lead SOT-23



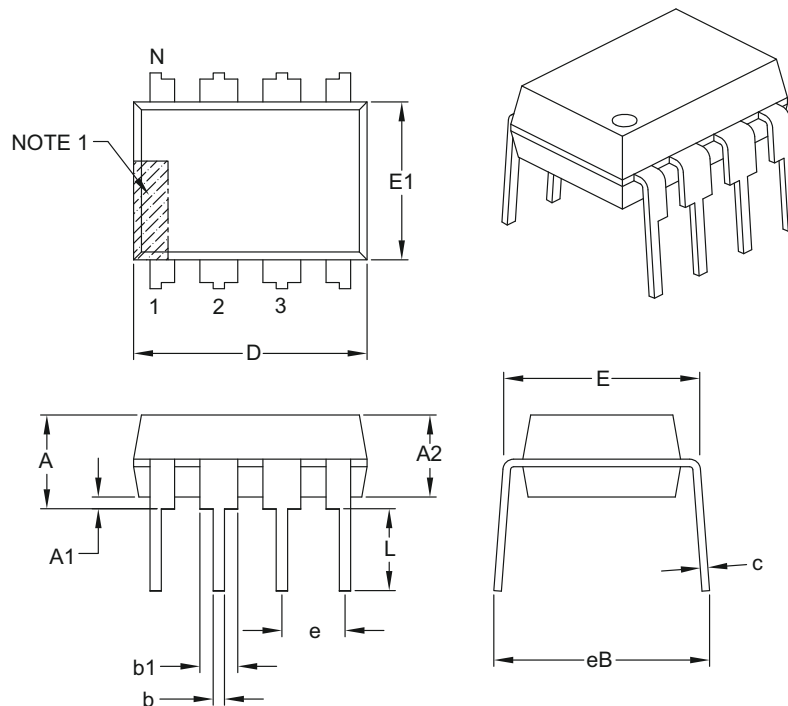
Example:



25AA010A/25LC010A

8-Lead Plastic Dual In-Line (P) – 300 mil Body [PDIP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	INCHES		
		MIN	NOM	MAX
Number of Pins	N	8		
Pitch	e	.100 BSC		
Top to Seating Plane	A	–	–	.210
Molded Package Thickness	A2	.115	.130	.195
Base to Seating Plane	A1	.015	–	–
Shoulder to Shoulder Width	E	.290	.310	.325
Molded Package Width	E1	.240	.250	.280
Overall Length	D	.348	.365	.400
Tip to Seating Plane	L	.115	.130	.150
Lead Thickness	c	.008	.010	.015
Upper Lead Width	b1	.040	.060	.070
Lower Lead Width	b	.014	.018	.022
Overall Row Spacing §	eB	–	–	.430

Notes:

- Pin 1 visual index feature may vary, but must be located with the hatched area.
- § Significant Characteristic.
- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" per side.
- Dimensioning and tolerancing per ASME Y14.5M.

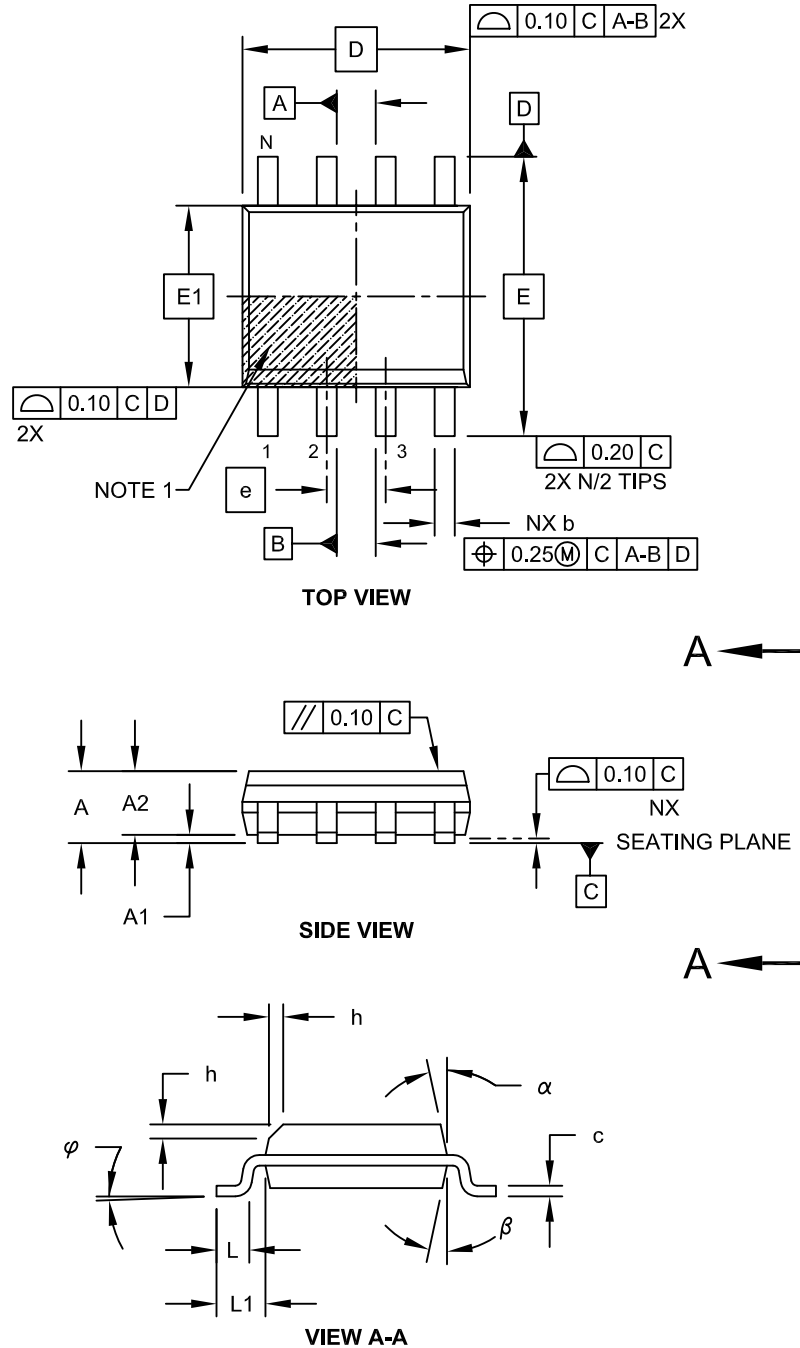
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-018B

25AA010A/25LC010A

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>

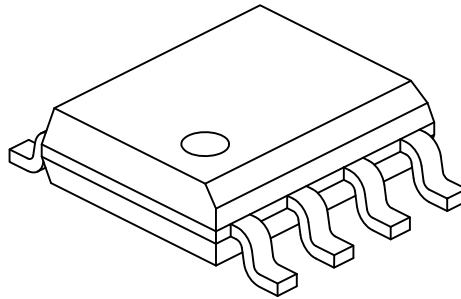


Microchip Technology Drawing No. C04-057C Sheet 1 of 2

25AA010A/25LC010A

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	8		
Pitch	e	1.27 BSC		
Overall Height	A	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	4.90 BSC		
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40	-	1.27
Footprint	L1	1.04 REF		
Foot Angle	φ	0°	-	8°
Lead Thickness	c	0.17	-	0.25
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5°	-	15°

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. § Significant Characteristic
3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

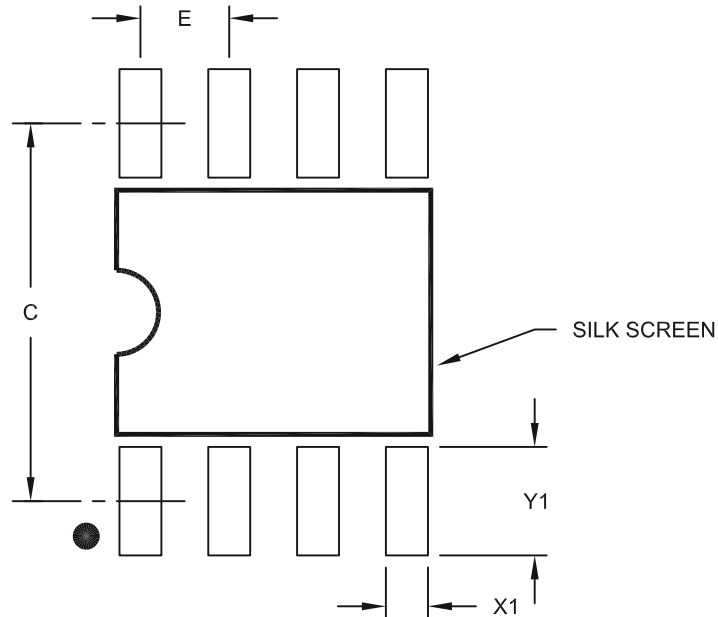
REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

25AA010A/25LC010A

8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	C		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

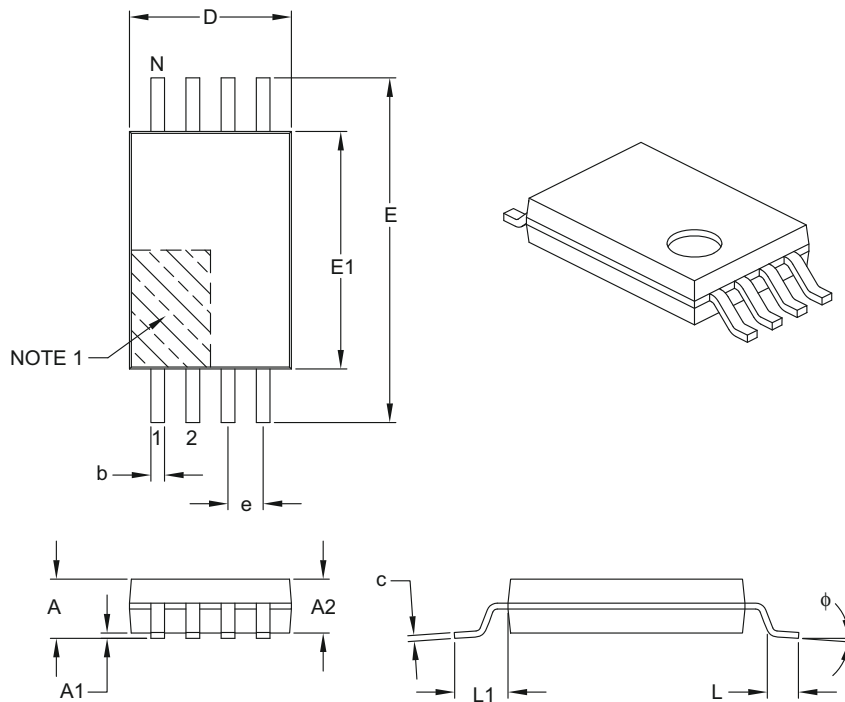
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

25AA010A/25LC010A

8-Lead Plastic Thin Shrink Small Outline (ST) – 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	8		
Pitch	e	0.65 BSC		
Overall Height	A	–	–	1.20
Molded Package Thickness	A2	0.80	1.00	1.05
Standoff	A1	0.05	–	0.15
Overall Width	E	6.40 BSC		
Molded Package Width	E1	4.30	4.40	4.50
Molded Package Length	D	2.90	3.00	3.10
Foot Length	L	0.45	0.60	0.75
Footprint	L1	1.00 REF		
Foot Angle	ϕ	0°	–	8°
Lead Thickness	c	0.09	–	0.20
Lead Width	b	0.19	–	0.30

Notes:

- Pin 1 visual index feature may vary, but must be located within the hatched area.
- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15 mm per side.
- Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

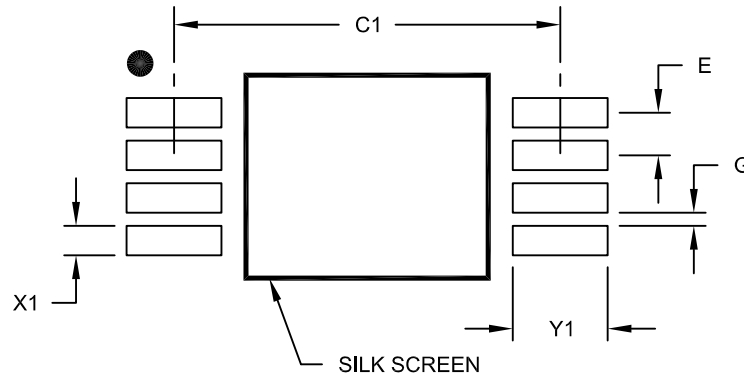
REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-086B

25AA010A/25LC010A

8-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.65 BSC		
Contact Pad Spacing	C1		5.90	
Contact Pad Width (X8)	X1			0.45
Contact Pad Length (X8)	Y1			1.45
Distance Between Pads	G	0.20		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

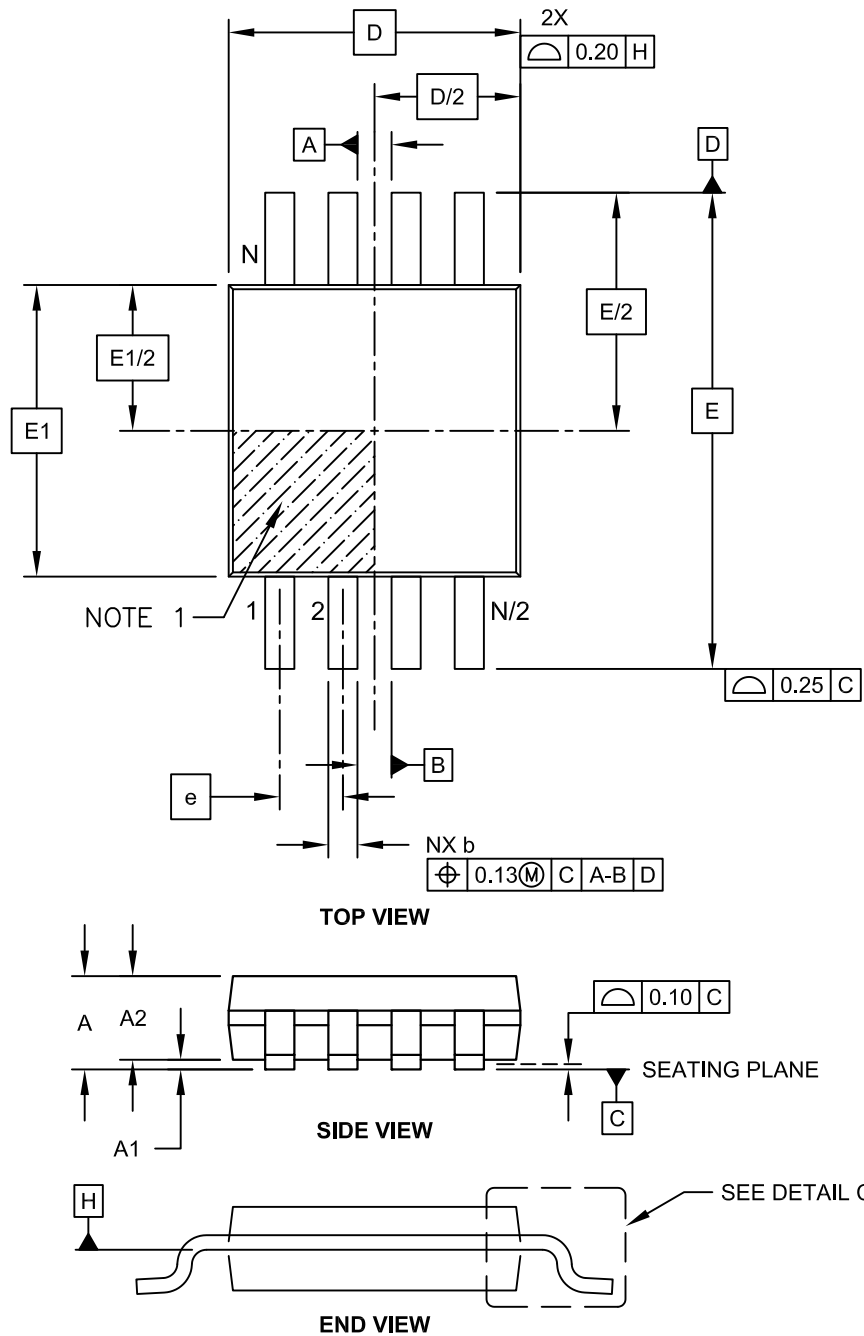
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2086A

25AA010A/25LC010A

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>

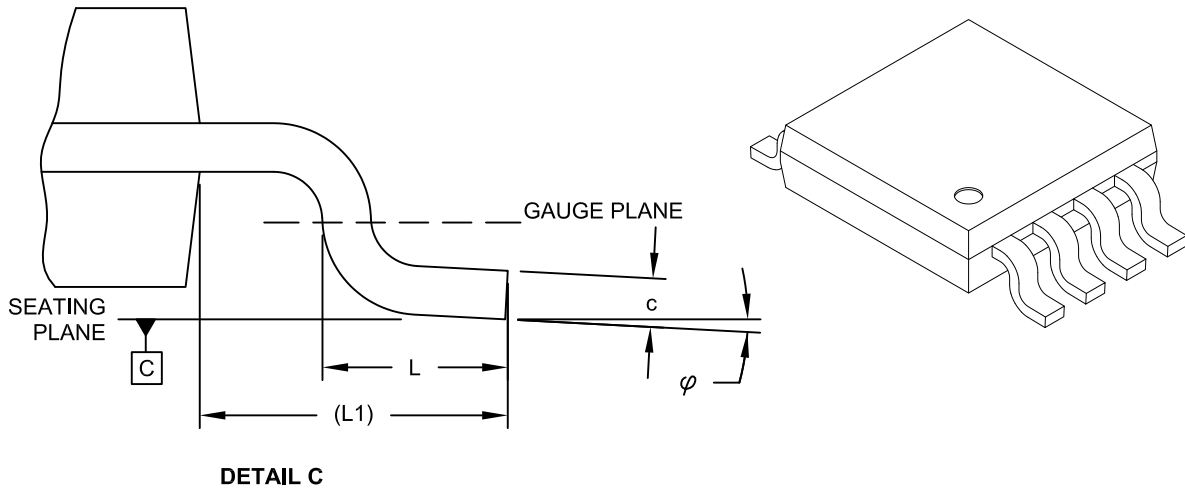


Microchip Technology Drawing C04-111C Sheet 1 of 2

25AA010A/25LC010A

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e	0.65 BSC		
Overall Height	A	-	-	1.10
Molded Package Thickness	A2	0.75	0.85	0.95
Standoff	A1	0.00	-	0.15
Overall Width	E	4.90 BSC		
Molded Package Width	E1	3.00 BSC		
Overall Length	D	3.00 BSC		
Foot Length	L	0.40	0.60	0.80
Footprint	L1	0.95 REF		
Foot Angle	φ	0°	-	8°
Lead Thickness	c	0.08	-	0.23
Lead Width	b	0.22	-	0.40

Notes:

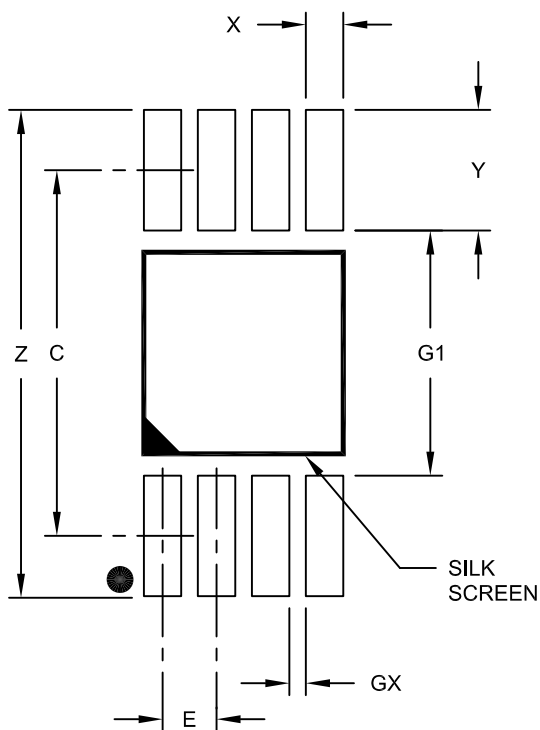
- Pin 1 visual index feature may vary, but must be located within the hatched area.
- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- Dimensioning and tolerancing per ASME Y14.5M.
 BSC: Basic Dimension. Theoretically exact value shown without tolerances.
 REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-111C Sheet 2 of 2

25AA010A/25LC010A

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.65 BSC		
Contact Pad Spacing	C		4.40	
Overall Width	Z			5.85
Contact Pad Width (X8)	X1			0.45
Contact Pad Length (X8)	Y1			1.45
Distance Between Pads	G1	2.95		
Distance Between Pads	GX	0.20		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

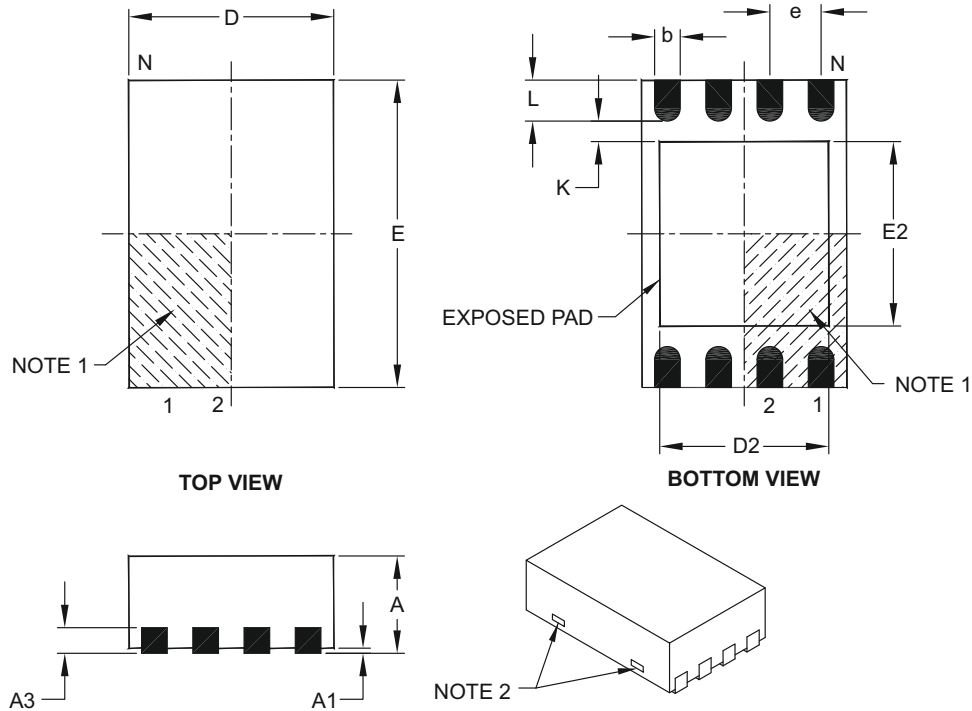
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2111A

25AA010A/25LC010A

8-Lead Plastic Dual Flat, No Lead Package (MC) – 2x3x0.9 mm Body [DFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	8		
Pitch	e	0.50 BSC		
Overall Height	A	0.80	0.90	1.00
Standoff	A1	0.00	0.02	0.05
Contact Thickness	A3	0.20 REF		
Overall Length	D	2.00 BSC		
Overall Width	E	3.00 BSC		
Exposed Pad Length	D2	1.30	–	1.55
Exposed Pad Width	E2	1.50	–	1.75
Contact Width	b	0.20	0.25	0.30
Contact Length	L	0.30	0.40	0.50
Contact-to-Exposed Pad	K	0.20	–	–

Notes:

- Pin 1 visual index feature may vary, but must be located within the hatched area.
- Package may have one or more exposed tie bars at ends.
- Package is saw singulated.
- Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-123C